

# **PN3569**

# **NPN General Purpose Amplifier**

• This device is designed for use at general purpose amplifiers and switches requiring collecor currents to 300mA.



### 1. Emitter 2. Base 3. Collector

# **Absolute Maximum Ratings\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above whitch the serviceability of any semiconductor device may be impaird.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

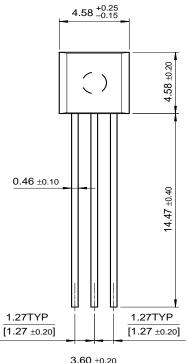
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
V <sub>(BR)CEO</sub>	Collector-Emitter Sustaining Voltage *	$I_C = 30\mu A, I_B = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	80		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 40V, I_{E} = 0$		50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4.0V, I_{C} = 0$		25	nA
On Characte	eristics			•	•
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = 1V, I <sub>C</sub> = 150mA	100	300	
		$V_{CE} = 1V$ , $I_C = 30mA$	100		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$		0.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	I <sub>C</sub> = 150mA, V <sub>CE</sub> = 1V		1.1	V
Small Signa	I Characteristics				
h <sub>fe</sub>	Small Signal current Gain	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V, f = 10MHz	3.0	30	
Pulse Test: Pulse	Width ≤ 300μs, Duty Cycle ≤ 2.0%				•

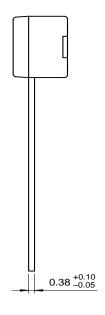
# Thermal Characteristics T<sub>a</sub>=25°C unless otherwise noted

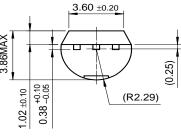
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# **Package Dimensions**

TO-92







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